

N-channel TrenchMOS standard level FET

Rev. 02 — 16 June 2010

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

#### 1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Suitable for standard level gate drive sources

Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1.	Quick reference da	ta				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	5.5	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	8	W
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 150 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	278	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ $T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 13</u>	-	128	150	mΩ
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 5 \text{ A};  V_{sup} \leq 55 \text{ V}; \\ R_{GS} &= 50  \Omega;  V_{GS} = 10  \text{ V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	25	mJ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain		
3	S	source		
4	D	drain		G-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-CI-
				mbb076 S
			SOT223 (SC-73)	

### 3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BUK78150-55A	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223		

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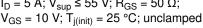
#### **Limiting values** 4.

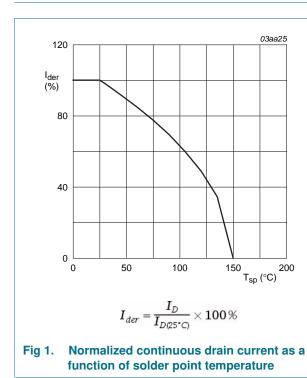
#### **Limiting values** Table 4.

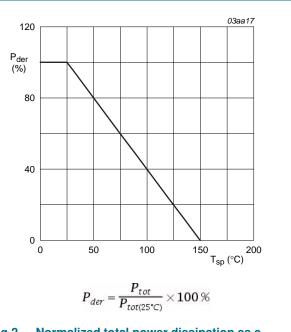
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 150 °C	-	-	55	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	-	55	V
V <sub>GS</sub>	gate-source voltage		-20	-	20	V
I <sub>D</sub>	drain current	$T_{sp} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{\text{Figure 3}};$	-	-	5.5	A
		$T_{sp}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	-	-	3.8	А
I <sub>DM</sub>	peak drain current	$T_{sp}$ = 25 °C; $t_p \le 10 \ \mu s$ ; pulsed; see Figure 3	-	-	22	A
P <sub>tot</sub>	total power dissipation	T <sub>sp</sub> = 25 °C; see <u>Figure 2</u>	-	-	8	W
T <sub>stg</sub>	storage temperature		-55	-	150	°C
Tj	junction temperature		-55	-	150	°C
Source-drai	in diode					
ls	source current	T <sub>sp</sub> = 25 °C	-	-	5.5	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{sp} = 25 \ ^{\circ}C$	-	-	22	А
Avalanche I	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source	$I_D = 5$ A; $V_{sup} ≤ 55$ V; $R_{GS} = 50$ Ω; Voc = 10 V: Tiggin = 25 °C: upclamped	-	-	25	mJ

drain-source avalanche energy



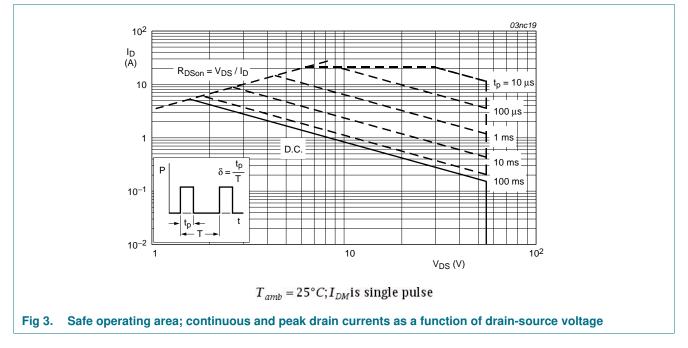






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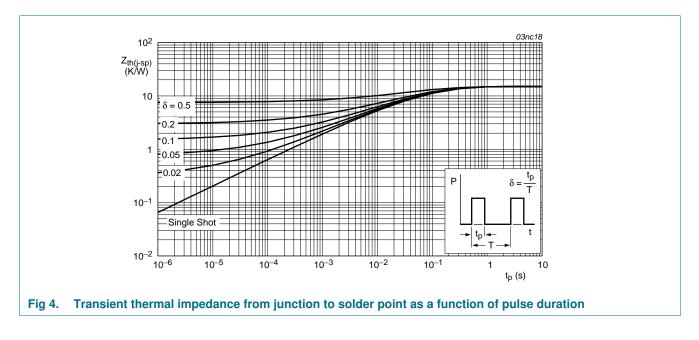
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#### 5. Thermal characteristics

#### Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Mi	n Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	15	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	see <u>Figure 4</u>	-	70	-	K/W



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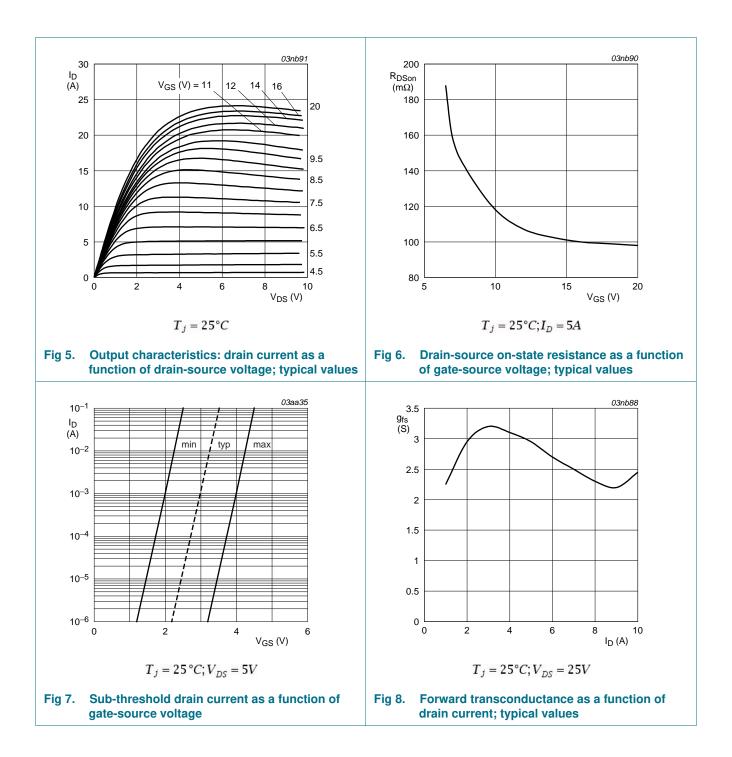
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#### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11	2	3	4	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 150 °C; see <u>Figure 11</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see Figure 11	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	500	μA
		V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		$V_{DS} = 0 V; V_{GS} = -20 V; T_j = 25 °C$	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 5 A; $T_j$ = 150 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	278	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 5 A; $T_j$ = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	128	150	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	170	230	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	54	65	pF
C <sub>rss</sub>	reverse transfer capacitance		-	37	52	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	3	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	26	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	8	-	ns
t <sub>f</sub>	fall time		-	10	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 5 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 10 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s};$	-	32	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	50	-	nC

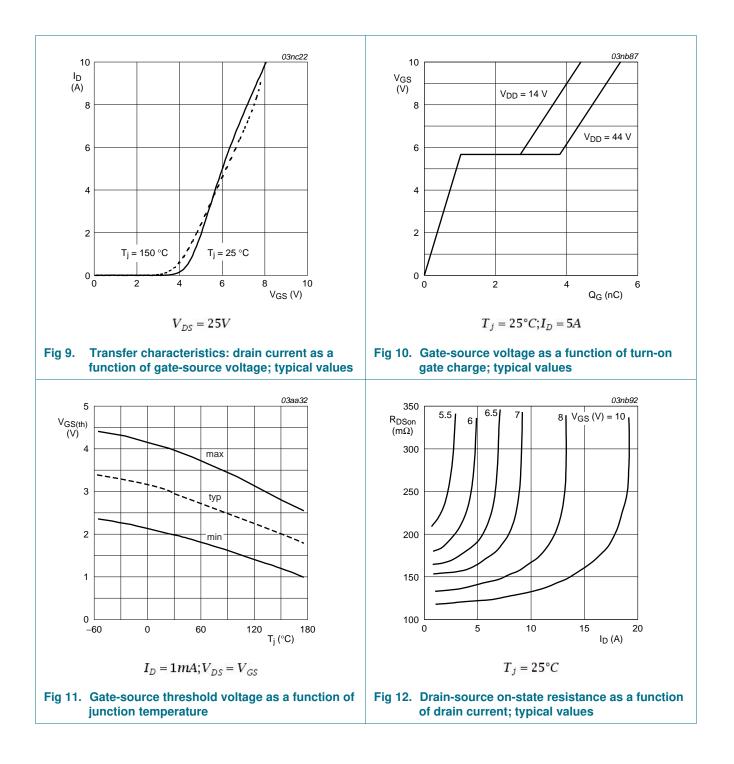
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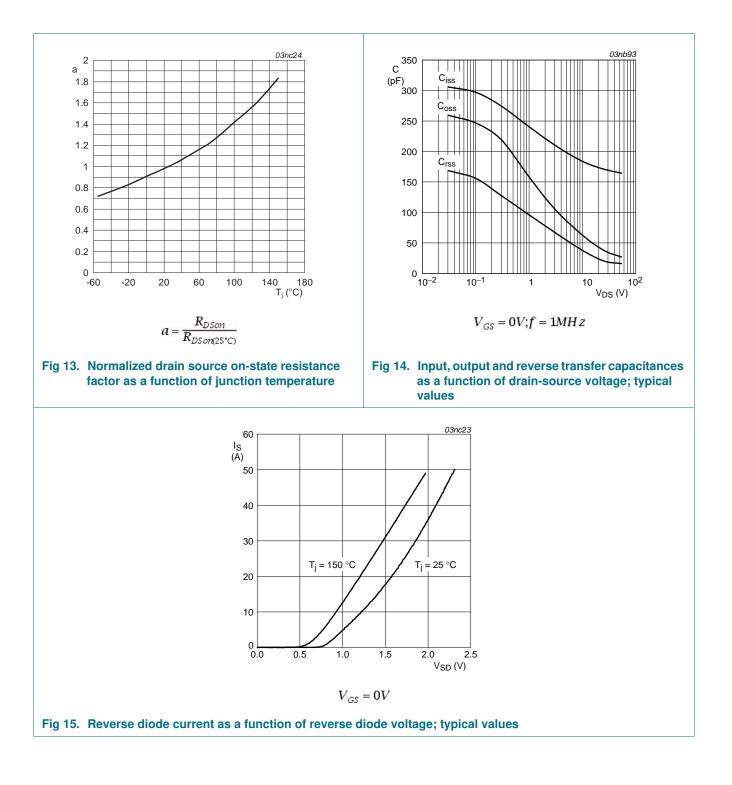
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#### 7. Package outline

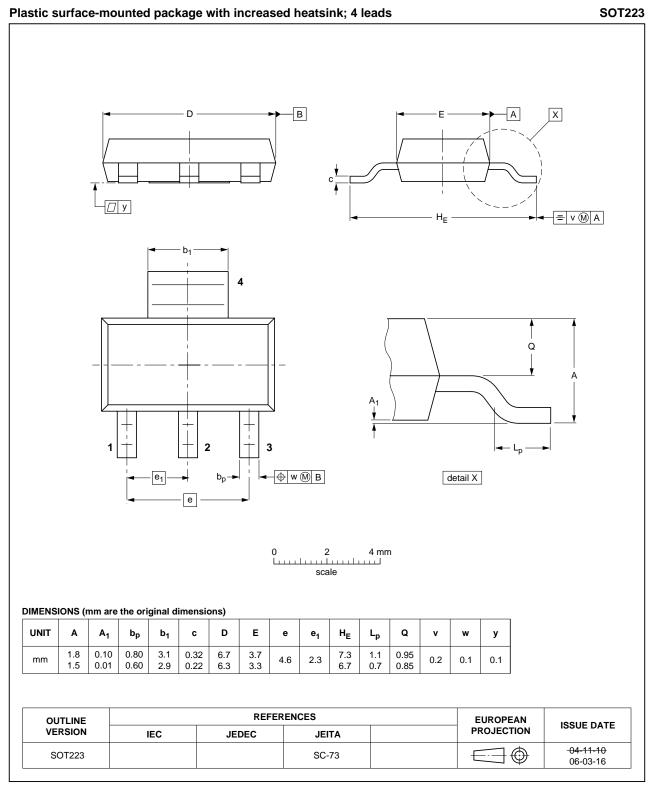


Fig 16. Package outline SOT223 (SC-73)

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### 8. Revision history

Table 7. Revision h	istory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK78150-55A v.2	20100616	Product data sheet	-	BUK78150-55A v.1
Modifications:	of NXP Se	miconductors	en redesigned to comply ne new company name w	with the new identity guidelines here appropriate.
BUK78150-55A v.1 (9397 750 07738)	20010130	Product Specification	-	-

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#### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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